



ACJT610-8F 6A TRIACs

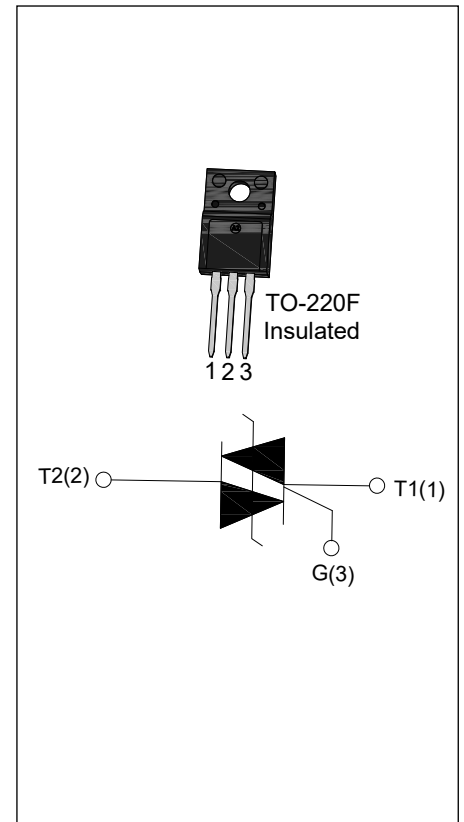
Rev.1.0

DESCRIPTION:

The ACJT610-8F of double mesa technology provide high interference immunity, They can be used as an static ON/OFF function in electrical control system, and used as a driver of low power and high inductance or resistive loads, such as jet pumps of dishwashers, fans of air-conditioner ... From all three terminals to external heatsink ACJT610-8F provides a rated insulation voltage of 2000 V_{RMS} , complying with UL standards (File ref: E252906). Packages TO-220F is RoHS compliant (2011/65/EU).

MAIN FEATURES

| Symbol | Value | Unit |
|--------------------|----------|------|
| $I_{T(RMS)}$ | 6 | A |
| V_{DRM}/V_{RRM} | 800 | V |
| $I_{GT\ I/II/III}$ | 10/10/10 | mA |



BSOLUTE MAXIMUM RATINGS

| Parameter | | Symbol | Value | Unit |
|---------------------------------------------------------------------|----------------------------------------|--------------|-----------|-------------|
| Storage junction temperature range | | T_{stg} | -40 – 150 | $^{\circ}C$ |
| Operating junction temperature range | | T_j | -40 – 125 | $^{\circ}C$ |
| Repetitive peak off-state voltage ($T_j=25^{\circ}C$) | | V_{DRM} | 800 | V |
| Repetitive peak reverse voltage ($T_j=25^{\circ}C$) | | V_{RRM} | 800 | V |
| RMS on-state current | TO-220F(Ins) ($T_C=103^{\circ}C$) | $I_{T(RMS)}$ | 6 | A |
| Non repetitive surge peak on-state current (full cycle, F=50Hz) | | I_{TSM} | 60 | A |
| Non repetitive surge peak on-state current (full cycle, F=60Hz) | | | 66 | A |
| I^2t value for fusing ($t_p=10ms$) | | I^2t | 18 | A^2s |
| Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$) | I - II -III | di/dt | 100 | $A/\mu s$ |

| | | | |
|------------------------------------------------------------------------------------|-------------|----|----|
| Peak gate current | I_{GM} | 4 | A |
| Average gate power dissipation | $P_{G(AV)}$ | 1 | W |
| Peak gate power | P_{GM} | 10 | W |
| Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.7) | V_{pp} | 3 | kV |

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

| Symbol | Test Condition | Quadrant | | Value | Unit |
|----------|----------------------------------------------------------------|-------------|-----|-------|------------------|
| I_{GT} | $V_D=12\text{V } R_L=30\Omega$ | I - II -III | MAX | 10 | mA |
| V_{GT} | | I - II -III | MAX | 1 | V |
| V_{GD} | $V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$ | I - II -III | MIN | 0.2 | V |
| I_L | $I_G=1.2I_{GT}$ | I -III | MAX | 20 | mA |
| | | II | | 35 | |
| I_H | $I_{TM}=0.2\text{A}$ | | MAX | 20 | mA |
| dv/dt | $V_D=540\text{V}$ Gate Open $T_j=125^\circ\text{C}$ | | MIN | 1000 | V/ μs |

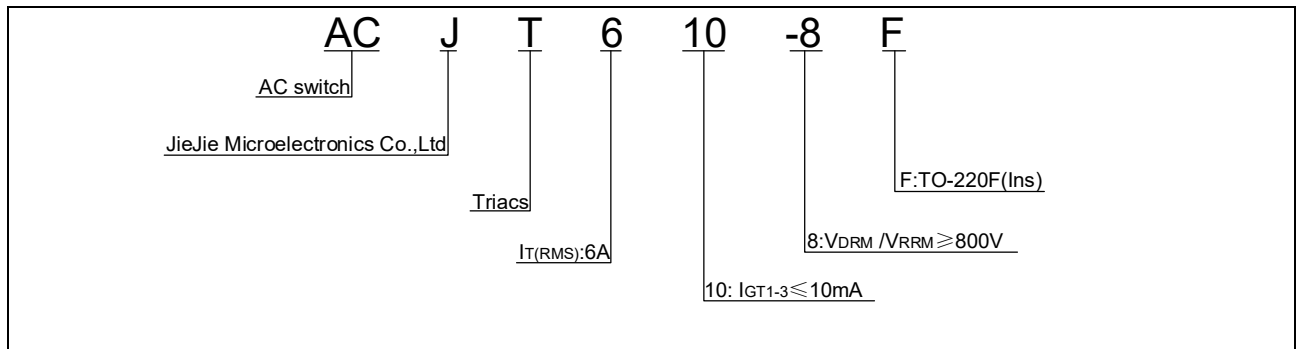
STATIC CHARACTERISTICS

| Symbol | Parameter | | Value(MAX) | Unit |
|-----------|------------------------------------------|-------------------------|------------|---------------|
| V_{TM} | $I_{TM}=8.5\text{A } t_p=380\mu\text{s}$ | $T_j=25^\circ\text{C}$ | 1.5 | V |
| V_{TO} | Threshold voltage | $T_j=125^\circ\text{C}$ | 0.94 | V |
| R_d | Dynamic resistance | $T_j=125^\circ\text{C}$ | 0.04 | Ω |
| I_{DRM} | $V_D=V_{DRM} V_R=V_{RRM}$ | $T_j=25^\circ\text{C}$ | 5 | μA |
| I_{RRM} | | $T_j=125^\circ\text{C}$ | 0.5 | mA |

THERMAL RESISTANCES

| Symbol | Parameter | | Value | Unit |
|---------------|----------------------|--------------|-------|---------------------------|
| $R_{th(j-c)}$ | junction to case(AC) | TO-220F(Ins) | 2.7 | $^\circ\text{C}/\text{W}$ |

ORDERING INFORMATION



MARKING

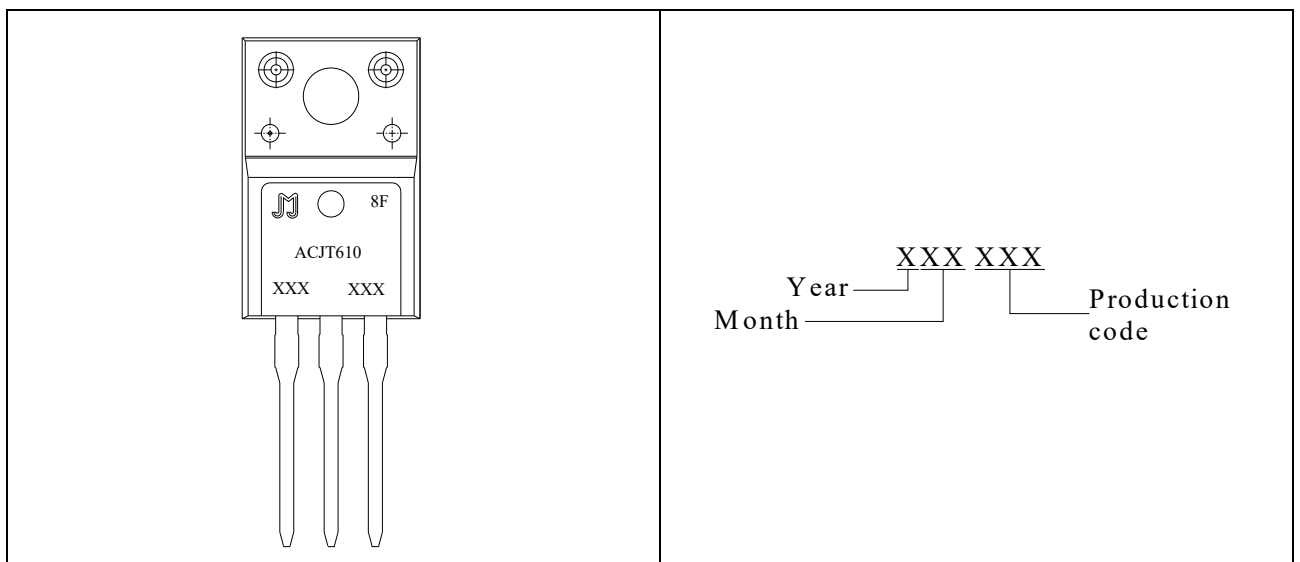


FIG.1: Maximum power dissipation versus RMS on-state current

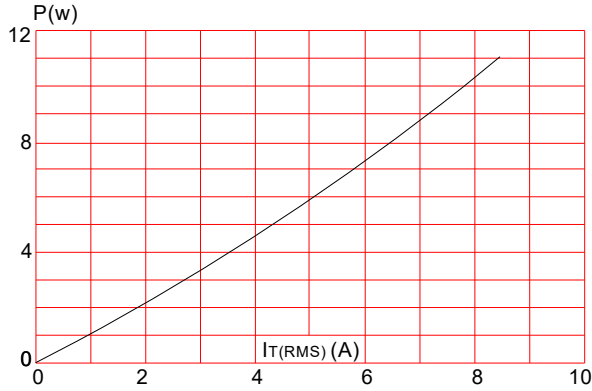


FIG.2: RMS on-state current versus case temperature

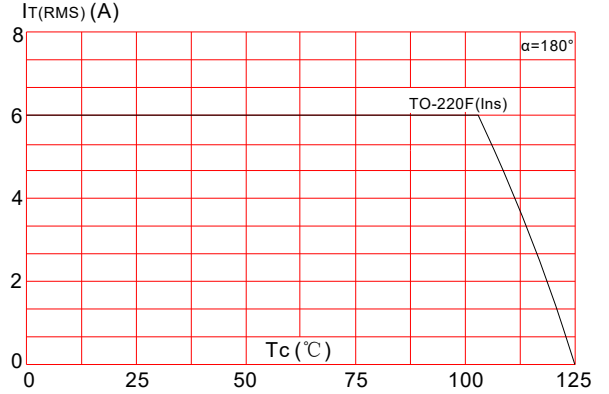


FIG.3: Surge peak on-state current versus number of cycles

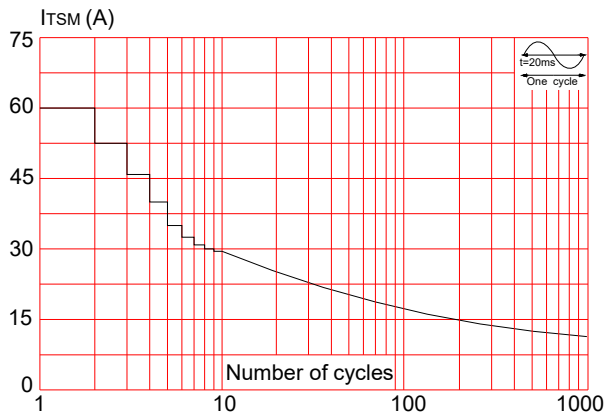


FIG.4: On-state characteristics (maximum values)

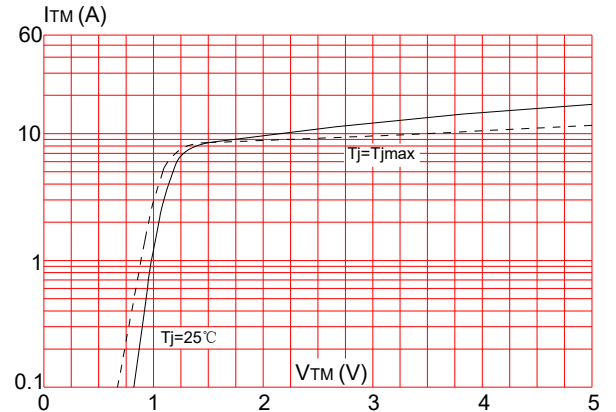


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

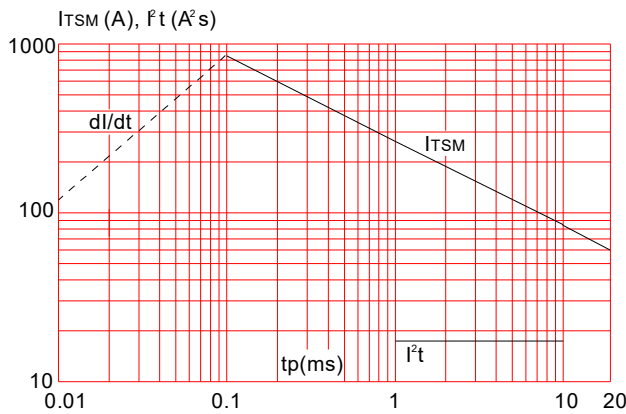


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

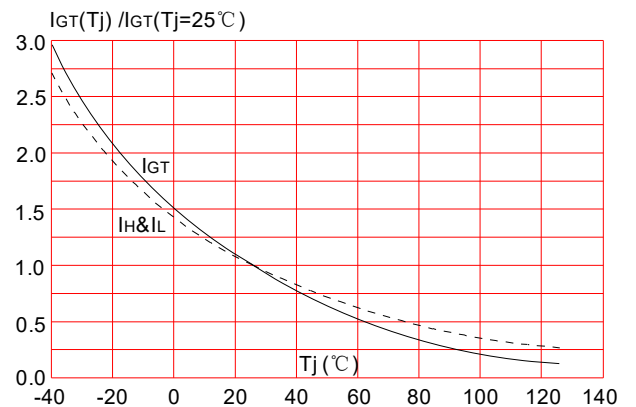
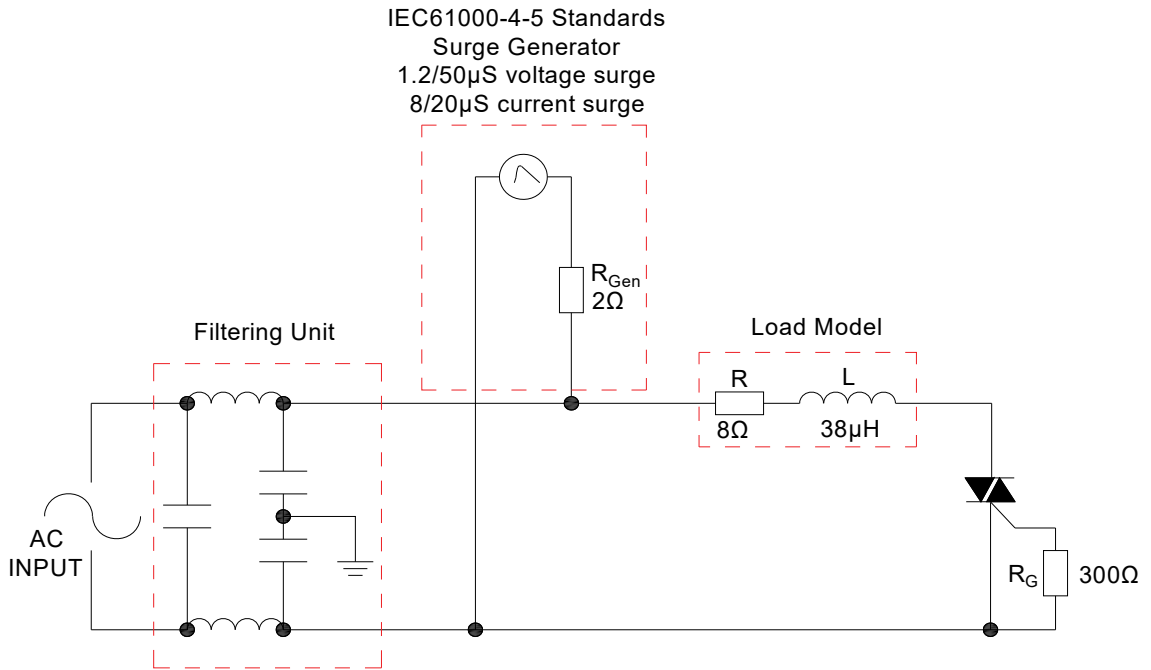


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



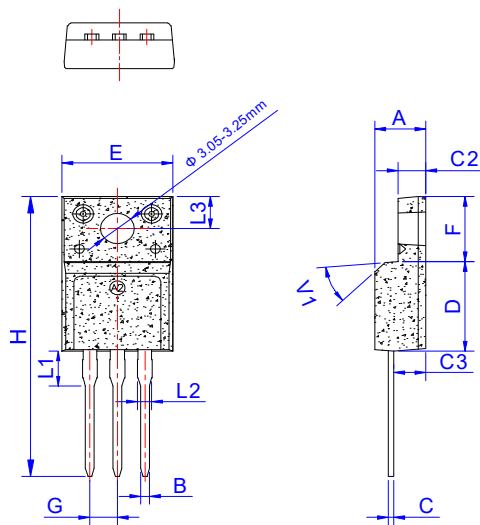
ORDERING INFORMATION

| Order code | Voltage V_{DRM}/V_{RRM} (V) | IGT(mA) | Package | Base qty. (pcs) | Delivery mode |
|------------|----------------------------------|--------------|--------------|--------------------|---------------|
| | | I - II - III | | | |
| ACJT610-8F | 800 | 10 | TO-220F(Ins) | 50 | Tube |

Document Revision History

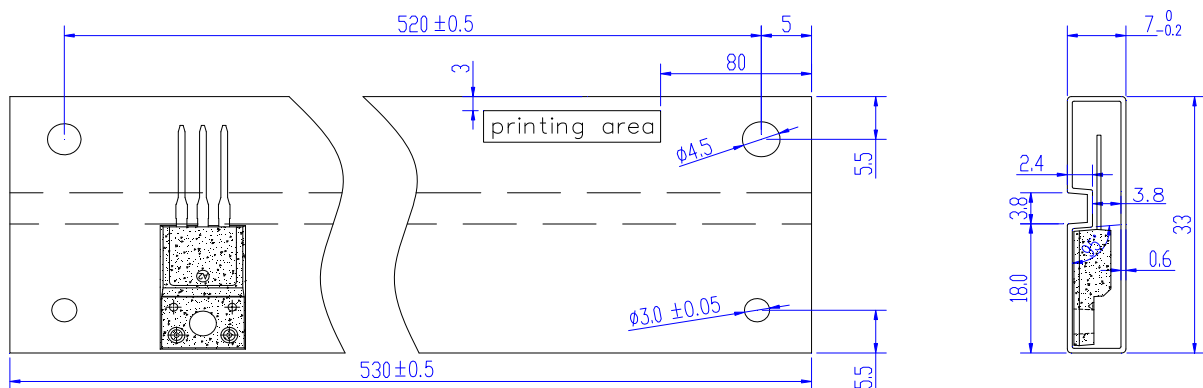
| Date | Revision | Changes |
|--------------|----------|-------------|
| Dec 09, 2022 | 1.0 | Last update |

PACKAGE MECHANICAL DATA



| Ref. | Dimensions | | | | | |
|------|-------------|------|------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 4.50 | | 4.90 | 0.177 | | 0.193 |
| B | 0.74 | 0.80 | 0.83 | 0.029 | 0.031 | 0.033 |
| C | 0.47 | | 0.65 | 0.019 | | 0.026 |
| C2 | 2.45 | | 2.75 | 0.096 | | 0.108 |
| C3 | 2.60 | | 3.00 | 0.102 | | 0.118 |
| D | 8.80 | | 9.30 | 0.346 | | 0.366 |
| E | 9.80 | | 10.4 | 0.386 | | 0.410 |
| F | 6.40 | | 6.80 | 0.252 | | 0.268 |
| G | 2.40 | | 2.70 | 0.094 | | 0.106 |
| H | 28.0 | | 29.8 | 1.102 | | 1.173 |
| L1 | 3.20 | | 3.80 | 0.126 | | 0.150 |
| L2 | 1.14 | | 1.70 | 0.045 | | 0.067 |
| L3 | 3.20 | | 3.60 | 0.126 | | 0.142 |
| V1 | | 45° | | | 45° | |


DELIVERY MODE



| PACKAGE | OUTLINE | TUBE (PCS) | INNER BOX (PCS) | PER CARTON |
|---------|---------|------------|-----------------|------------|
| TO-220F | TUBE | 50 | 1,000 | 5,000 |



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